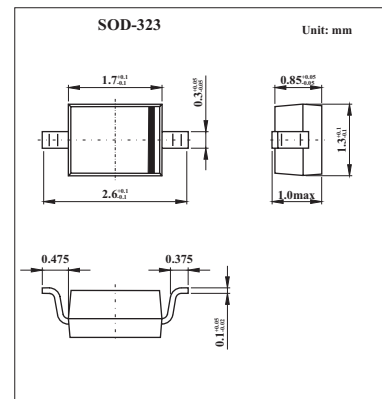


SILICON SWITCHING DIODE

BAS16-03W

■ Features

- For high-speed Switching applications



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Value	Unit
Diode reverse voltage	V _R	80	V
Peak reverse voltage	V _{RM}	85	
Forward current	I _F	250	mA
Non-repetitive peak surge forward current	I _{FSM}	4.5	A
Total power dissipation	P _{tot}	250	mW
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-65 to +150	
Junction soldering point ⁽¹⁾	R _{thjS}	≤ 135	K/W

Note:

1. For calculation of R_{thJA} please refer to Application Note Thermal Resistance

SILICON SWITCHING DIODE

BAS16-03W

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min	Typ	Max	Unit
Breakdown voltage $I_{(BR)} = 100 \mu\text{A}$	$V_{(BR)}$	85			V
Reverse current $V_R = 75\text{V}$ $V_R = 25\text{V}, T_a = 150^\circ\text{C}$ $V_R = 75\text{V}, T_a = 150^\circ\text{C}$	I_R			0.1	μA
				30	
				50	
Forward voltage $I_F = 1\text{mA}$ $I_F = 10\text{mA}$ $I_F = 50\text{mA}$ $I_F = 100\text{mA}$ $I_F = 150\text{mA}$	V_F			715	mV
				855	
				1000	
				1200	
				1250	
Forward recovery voltage $I_F = 10\text{mA}, t_p = 20\text{ns}$	V_{fr}			1.75	V
Diode capacitance $V_R = 0; f = 1\text{MHz}$	C_T			2	V
Reverse Recovery Time $I_F = 10\text{mA}; I_R = 10\text{mA};$ measured at $I_R = 1\text{mA}, R_L = 100\Omega$	t_{rr}			4	nS

■ Marking

Marking	B
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